

Abstract Submitted  
for the MAR16 Meeting of  
The American Physical Society

**XPS characterization scheme for phase-pure epitaxial NbO<sub>2</sub>** TOBIAS HADAMEK, AGHAM POSADAS, ALEX DEMKOV, University of Texas at Austin — NbO<sub>2</sub> shows a semiconductor-to-metal transition with an associated structural transition of Peierls type. NbO<sub>2</sub> and Nb<sub>2</sub>O<sub>5</sub> or mixtures thereof have also shown electrically induced insulator-to-metal transitions. To shed light on the nature of the electrically induced insulator-to-metal transition it is important to grow high phase purity NbO<sub>2</sub> and Nb<sub>2</sub>O<sub>5</sub> and compare electrical measurements with mixed niobium oxides and with different electrode materials. Processing NbO<sub>2</sub> and avoiding surface oxidation requires ultra-high vacuum (UHV) conditions. Niobium oxide thin films were grown in UHV by molecular beam epitaxy on 111-oriented STO substrates and analyzed by X-ray photoelectron spectroscopy (XPS). It was shown that the NbO<sub>2</sub> 3d core level spectrum exhibits an asymmetric spin-orbit peak pair with more spectral weight on the high binding energy side. Based on the shape of the Nb 3d core levels, peak positions relative to the oxygen O 1s peak, and the valence band shape and height ratio of the niobium 4d<sub>xy</sub> split-off band to the oxygen 2p band, an identification scheme for NbO<sub>2</sub> by XPS was devised. Complementary the NbO<sub>2</sub> phase was confirmed by reflection high-energy electron and x-ray diffraction analysis.

Tobias Hadamek  
University of Texas at Austin

Date submitted: 24 Nov 2015

Electronic form version 1.4